

General Description

The WST4045 is the highest performance trench P-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WST4045 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

BVDSS	RDSON	ID
-40V	73mΩ	-4.3A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	-40	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ -10V	-4.3	А	
I _{DP}	Pulsed Drain Current	-20	A	
PD	Total Power Dissipation	2.0	W	
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 to 150	°C	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient		125	°C/W



WST4045

P-Ch MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-40			V
$\triangle BV_{DSS} / \triangle T_J$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=-1mA		-0.03		V/℃
Baaraa	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-3A		73	85	mΩ
R _{DS(ON)}		V _{GS} =-4.5V , I _D =-1A		98	126	
V _{GS(th)}	Gate Threshold Voltage		-1.0	-1.5	-3.0	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient			4.56		mV/℃
la se	Drain Source Lookage Current	V_{DS} =-28V , V_{GS} =0V , T_{J} =25 $^{\circ}$ C			1	- uA
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-28V , V_{GS} =0V , TJ=55 $^{\circ}$ C			5	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-3A		10		S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		3.8		Ω
Qg	Total Gate Charge (-4.5V)			14		
Q _{gs}	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-10V , I _D =-3.1A		2.9		nC
Q _{gd}	Gate-Drain Charge			3.8		
T _{d(on)}	Turn-On Delay Time			9		
Tr	Rise Time	V _{DD} =-20V , V _{GS} =-10V ,		8		
T _{d(off)}	Turn-Off Delay Time	R _G =3Ω, R∟=2Ω		28		ns
T _f	Fall Time			10		
C _{iss}	Input Capacitance			650		
Coss	Output Capacitance	V _{DS} =-20V , V _{GS} =0V , f=1MHz		90		pF
C _{rss}	Reverse Transfer Capacitance			70		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	$V_G = V_D = 0V$, Force Current			-4.3	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-2.5A			-1.2	V

Note :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

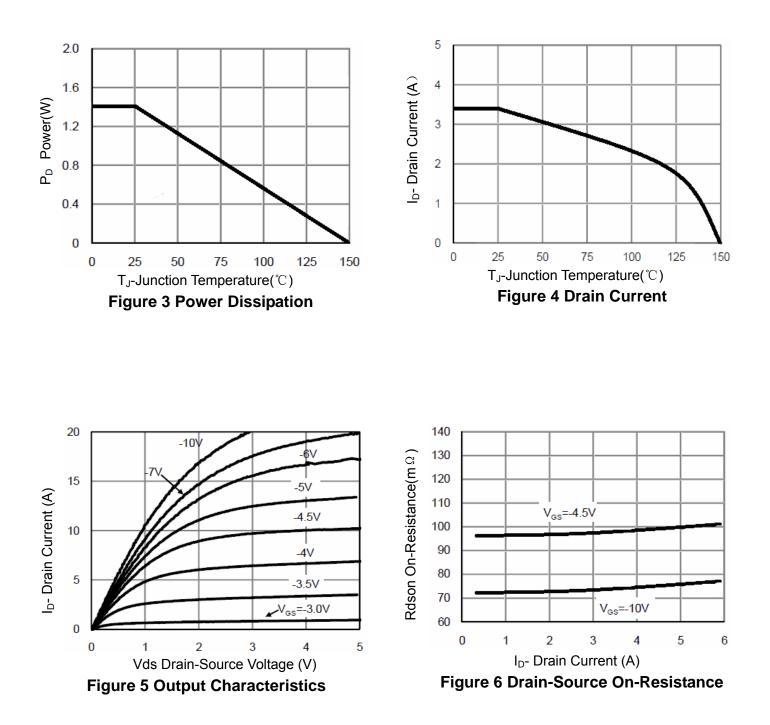
4. Guaranteed by design, not subject to production



WST4045

P-Ch MOSFET

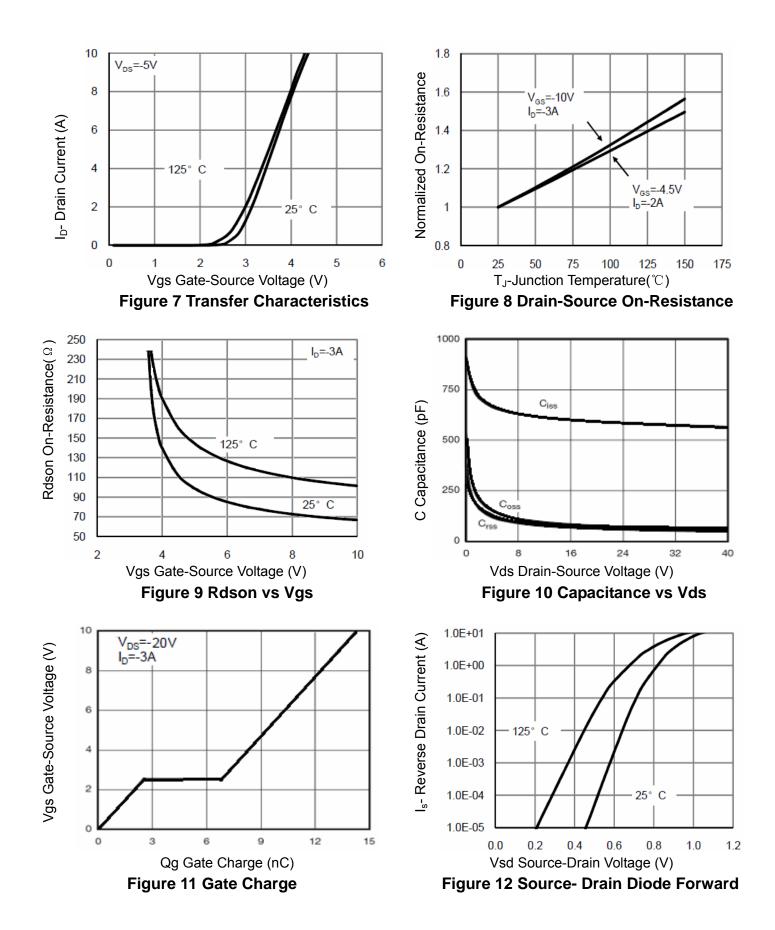
Typical Electrical and Thermal Characteristics





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P-Ch MOSFET







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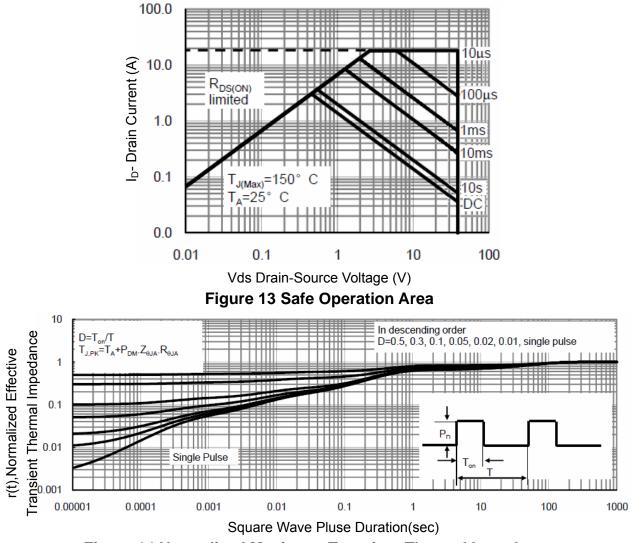


Figure 14 Normalized Maximum Transient Thermal Impedance



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